## SURFACE MOUNT SCHOTTKY BARRIER RECTIFIER

#### **Features**

- · Metal silicon junction, majority carrier conduction
- · Low power loss, high efficiency
- Guard ring for overvoltage protection
- · High current capability, low forward voltage drop
- · High surge capability
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications

# Solderable Ends $D_2$ $D_1 = \frac{1.7}{1.5}$ $D_2 = D_1^{10}$ $D_2 = D_1^{10}$ $D_2 = D_1^{10}$

Dimensions in millimeters MiniMELF (DO-213AA)

### **Mechanical Data**

- · Case: MiniMELF (DO-213AA), molded plastic body
- Terminals: Solder plated, solderable per MIL-STD-750, method 2026
- · Polarity: Color band denotes cathode end
- Mounting Position: Any

# **Absolute Maximum Ratings and Characteristics**

Ratings at 25 °C ambient temperature unless otherwise specified, single phase, half wave, resistive or inductive load. For capacitive load, derate by 20%

Parameter	Symbols	LM5817	LM5818	LM5819	Units
Maximum Repetitive Peak Reverse Voltage	$V_{RRM}$	20	30	40	V
Maximum RMS Voltage	$V_{RMS}$	14	21	28	V
Maximum DC Blocking Voltage	$V_{DC}$	20	30	40	V
Maximum Average Forward Rectified Current	I <sub>F(AV)</sub>		1		Α
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load(JEDEC methode)	I <sub>FSM</sub>		25		А
Maximum Instantaneous Forward Voltage at $I_F = 1 \text{ A}$	l V-	0.45	0.55	0.6	V
at $I_F = 3 A$		0.75	0.875	0.9	
Maximum Instantaneous Reverse Current at T <sub>A</sub> = 25 °C	0.5			mA	
Rated DC Blocking Voltage $^{1)}$ $T_A = 100  ^{\circ}C$	I <sub>R</sub>	10		111/5	
Typical Junction Capacitance 2)	CJ	110			pF
Typical Thermal Resistance, Junction to Ambient 3)	R <sub>0JA</sub> 75			°C/W	
Typical Thermal Resistance, Junction to Terminal 4)	$R_{\theta JL}$	30			O, VV
Operating Junction Temperature Range	T <sub>j</sub>	- 55 to + 125			°C
Storage Temperature Range	T <sub>stg</sub>	- 55 to + 150			°C

 $<sup>^{1)}\,\</sup>text{Pulse}$  test: 300  $\mu\text{s}$  pulse width, 1% duty cycle

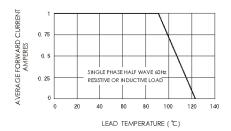


 $<sup>^{\</sup>rm 2)}$  Mearsured at 1 MHz and reverse voltage of 4 V

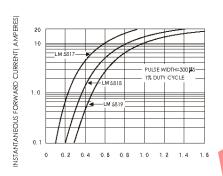
<sup>3)</sup> Thermal resistance junction to ambient 0.24" X 0.24"(6 X 6 mm) copper pads to each terminals

<sup>&</sup>lt;sup>4)</sup> Thermal resistance junction to terminal 0.24" X 0.24"(6 X 6 mm) copper pads to each terminals

#### FIG.1-FORWARD CURRENT DERATING CURVE

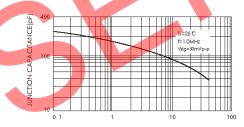


# FIG.3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

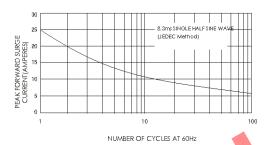


INSTANTANEOUS FORWARD VOLTAGE (VOLTS)

## FIG.5-TYPICAL JUNCTION CAPACITANCE



# FIG.2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT



#### FIG.4-TYPICAL REVERSE CHARACTERISTICS

